Abstracts

Microwave noise and power performance of metamorphic InP heterojunction bipolar transistors (Dec. 2001 [T-MTT])

S. Halder, Yong Zhong Xiong, Geok-Ing Ng, Hong Wang, Haiqun Zheng, K. Radhakrishnan and J.C.M. Hwang. "Microwave noise and power performance of metamorphic InP heterojunction bipolar transistors (Dec. 2001 [T-MTT])." 2001 Transactions on Microwave Theory and Techniques 49.12 (Dec. 2001 [T-MTT] (Special Issue on 2001 International Microwave Symposium)): 2408-2412.

For the first time, microwave noise and power performance of metamorphic InP heterojunction bipolar transistors (MM-HBTs) grown on GaAs substrates are reported. We find that microwave performance of MM-HBTs is comparable to that of lattice-matched InP heterojunction bipolar transistors of identical design. The preliminary results imply that the superior performance of InP heterojunction bipolar transistors can be confidently exploited with the more mature manufacturing technology of GaAs.

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